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Understanding Embedded - FPGAs (Field Programmable Gate Array)

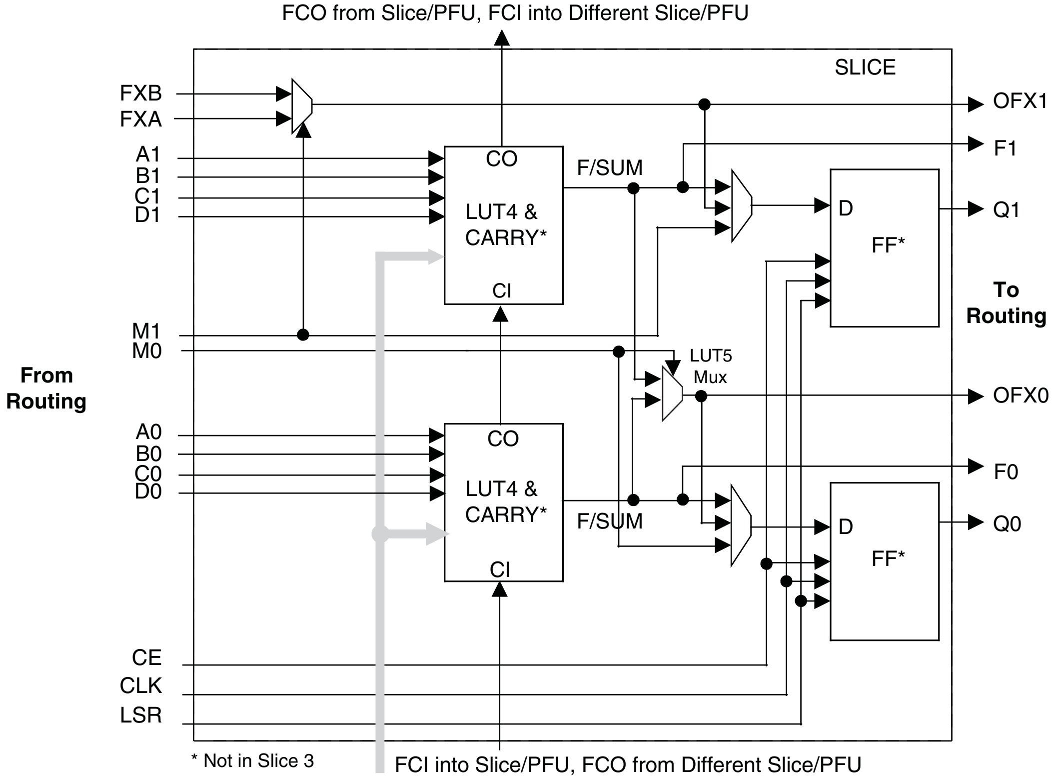
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	5000
Number of Logic Elements/Cells	40000
Total RAM Bits	906240
Number of I/O	363
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	484-BBGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfxp2-40e-6f484c

Figure 2-3. Slice Diagram



For Slices 0 and 2, memory control signals are generated from Slice 1 as follows:
WCK is CLK
WRE is from LSR
DI[3:2] for Slice 2 and DI[1:0] for Slice 0 data
WAD [A:D] is a 4bit address from slice 1 LUT input

Table 2-2. Slice Signal Descriptions

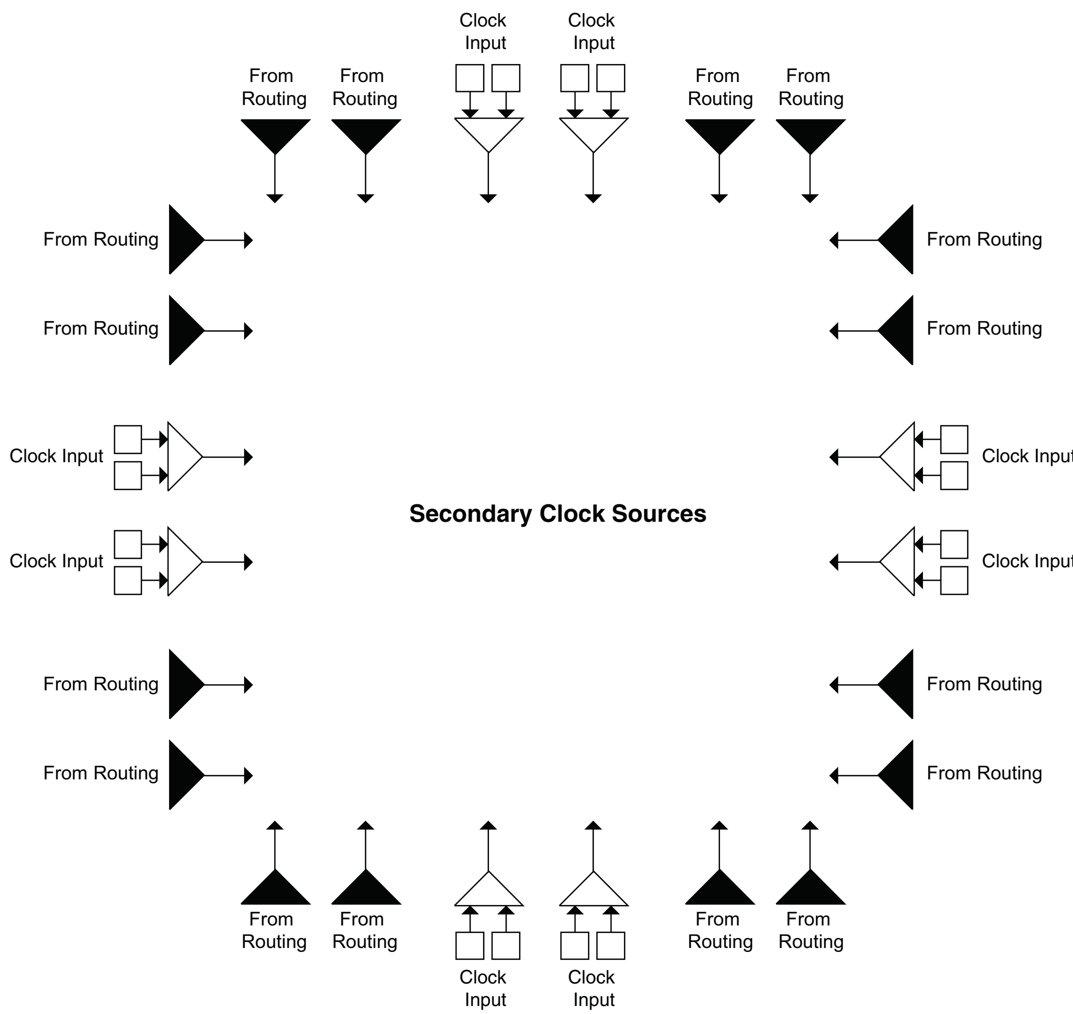
Function	Type	Signal Names	Description
Input	Data signal	A0, B0, C0, D0	Inputs to LUT4
Input	Data signal	A1, B1, C1, D1	Inputs to LUT4
Input	Multi-purpose	M0	Multipurpose Input
Input	Multi-purpose	M1	Multipurpose Input
Input	Control signal	CE	Clock Enable
Input	Control signal	LSR	Local Set/Reset
Input	Control signal	CLK	System Clock
Input	Inter-PFU signal	FCI	Fast Carry-In[1]
Input	Inter-slice signal	FXA	Intermediate signal to generate LUT6 and LUT7
Input	Inter-slice signal	FXB	Intermediate signal to generate LUT6 and LUT7
Output	Data signals	F0, F1	LUT4 output register bypass signals
Output	Data signals	Q0, Q1	Register outputs
Output	Data signals	OFX0	Output of a LUT5 MUX
Output	Data signals	OFX1	Output of a LUT6, LUT7, LUT8[2] MUX depending on the slice
Output	Inter-PFU signal	FCO	Slice 2 of each PFU is the fast carry chain output[1]

1. See Figure 2-3 for connection details.
2. Requires two PFUs.

Secondary Clock/Control Sources

LatticeXP2 devices derive secondary clocks (SC0 through SC7) from eight dedicated clock input pads and the rest from routing. Figure 2-7 shows the secondary clock sources.

Figure 2-7. Secondary Clock Sources



sysMEM Memory

LatticeXP2 devices contains a number of sysMEM Embedded Block RAM (EBR). The EBR consists of 18 Kbit RAM with dedicated input and output registers.

sysMEM Memory Block

The sysMEM block can implement single port, dual port or pseudo dual port memories. Each block can be used in a variety of depths and widths as shown in Table 2-5. FIFOs can be implemented in sysMEM EBR blocks by using support logic with PFUs. The EBR block supports an optional parity bit for each data byte to facilitate parity checking. EBR blocks provide byte-enable support for configurations with18-bit and 36-bit data widths.

Table 2-5. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36
True Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18
Pseudo Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36

Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

FlashBAK EBR Content Storage

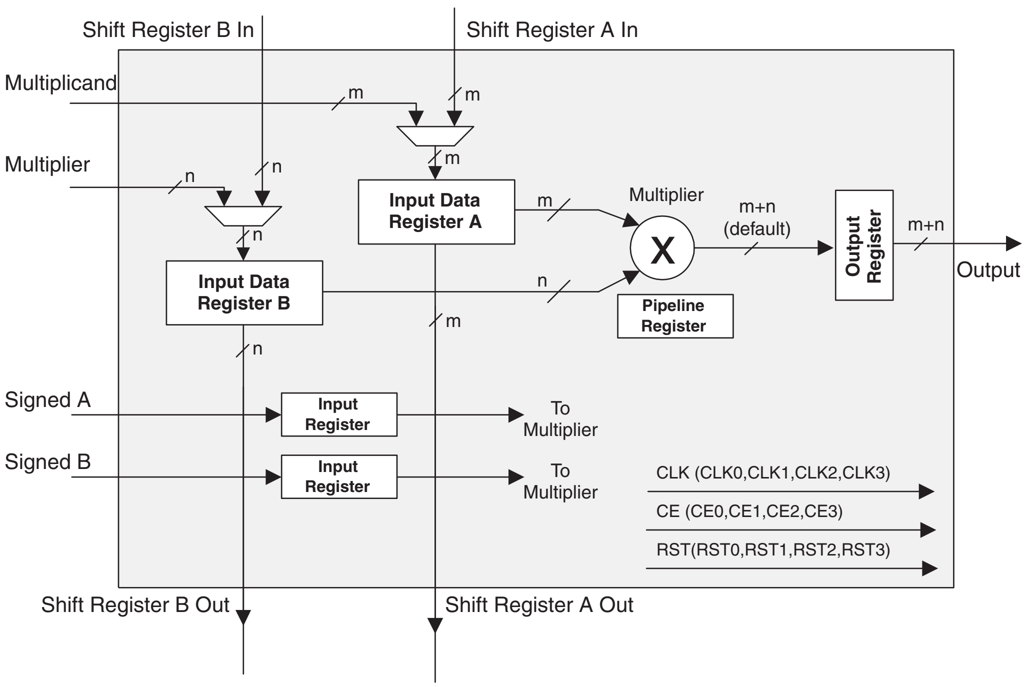
All the EBR memory in the LatticeXP2 is shadowed by Flash memory. Optionally, initialization values for the memory blocks can be defined using the Lattice Diamond design tools. The initialization values are loaded into the Flash memory during device programming and into the SRAM at power up or whenever the device is reconfigured. This feature is ideal for the storage of a variety of information such as look-up tables and microprocessor code. It is also possible to write the current contents of the EBR memory back to Flash memory. This capability is useful for the storage of data such as error codes and calibration information. For additional information on the FlashBAK capability see TN1137, LatticeXP2 Memory Usage Guide.

- In the ‘Signed/Unsigned’ options the operands can be switched between signed and unsigned on every cycle.
- In the ‘Add/Sub’ option the Accumulator can be switched between addition and subtraction on every cycle.
- The loading of operands can switch between parallel and serial operations.

MULT sysDSP Element

This multiplier element implements a multiply with no addition or accumulator nodes. The two operands, A and B, are multiplied and the result is available at the output. The user can enable the input/output and pipeline registers. Figure 2-20 shows the MULT sysDSP element.

Figure 2-20. MULT sysDSP Element



register. Similarly, CE and RST are selected from their four respective sources (CE0, CE1, CE2, CE3 and RST0, RST1, RST2, RST3) at each input register, pipeline register and output register.

Signed and Unsigned with Different Widths

The DSP block supports other widths, in addition to x9, x18 and x36 widths, of signed and unsigned multipliers. For unsigned operands, unused upper data bits should be filled to create a valid x9, x18 or x36 operand. For signed two's complement operands, sign extension of the most significant bit should be performed until x9, x18 or x36 width is reached. Table 2-7 provides an example of this.

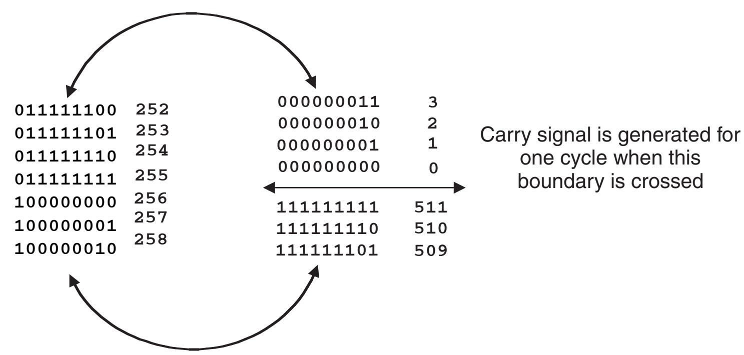
Table 2-7. Sign Extension Example

Number	Unsigned	Unsigned 9-bit	Unsigned 18-bit	Signed	Two's Complement Signed 9 Bits	Two's Complement Signed 18 Bits
+5	0101	000000101	000000000000000101	0101	000000101	000000000000000101
-6	N/A	N/A	N/A	1010	111111010	111111111111111010

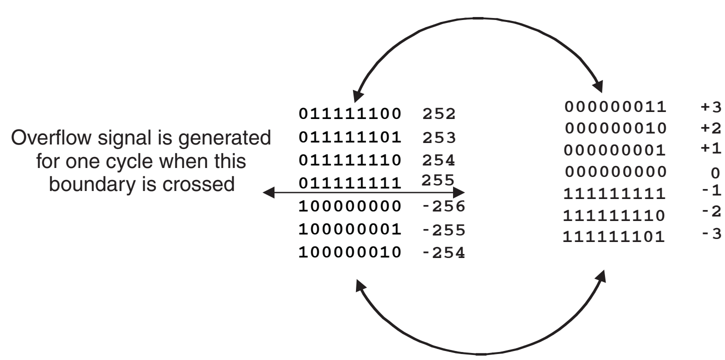
OVERFLOW Flag from MAC

The sysDSP block provides an overflow output to indicate that the accumulator has overflowed. "Roll-over" occurs and an overflow signal is indicated when any of the following is true: two unsigned numbers are added and the result is a smaller number than the accumulator, two positive numbers are added with a negative sum or two negative numbers are added with a positive sum. Note that when overflow occurs the overflow flag is present for only one cycle. By counting these overflow pulses in FPGA logic, larger accumulators can be constructed. The conditions for the overflow signal for signed and unsigned operands are listed in Figure 2-24.

Figure 2-24. Accumulator Overflow/Underflow



Unsigned Operation



Signed Operation

Tristate Register Block

The tristate register block provides the ability to register tri-state control signals from the core of the device before they are passed to the sysIO buffers. The block contains a register for SDR operation and an additional latch for DDR operation. Figure 2-27 shows the Tristate Register Block with the Output Block

In SDR mode, ONEG1 feeds one of the flip-flops that then feeds the output. The flip-flop can be configured as D-type or latch. In DDR mode, ONEG1 and OPOS1 are fed into registers on the positive edge of the clock. Then in the next clock the registered OPOS1 is latched. A multiplexer running off the same clock cycle selects the correct register for feeding to the output (D0).

Control Logic Block

The control logic block allows the selection and modification of control signals for use in the PIO block. A clock signal is selected from general purpose routing, ECLK1, ECLK2 or a DQS signal (from the programmable DQS pin) and is provided to the input register block. The clock can optionally be inverted.

DDR Memory Support

PICs have additional circuitry to allow implementation of high speed source synchronous and DDR memory interfaces.

PICs have registered elements that support DDR memory interfaces. Interfaces on the left and right edges are designed for DDR memories that support 16 bits of data, whereas interfaces on the top and bottom are designed for memories that support 18 bits of data. One of every 16 PIOs on the left and right and one of every 18 PIOs on the top and bottom contain delay elements to facilitate the generation of DQS signals. The DQS signals feed the DQS buses which span the set of 16 or 18 PIOs. Figure 2-28 and Figure 2-29 show the DQS pin assignments in each set of PIOs.

The exact DQS pins are shown in a dual function in the Logic Signal Connections table in this data sheet. Additional detail is provided in the Signal Descriptions table. The DQS signal from the bus is used to strobe the DDR data from the memory into input register blocks. For additional information on using DDR memory support please see TN1138, LatticeXP2 High Speed I/O Interface.

Table 2-13. Supported Output Standards

Output Standard	Drive	V_{CCIO} (Nom.)
Single-ended Interfaces		
LVTTL	4mA, 8mA, 12mA, 16mA, 20mA	3.3
LVCMOS33	4mA, 8mA, 12mA 16mA, 20mA	3.3
LVCMOS25	4mA, 8mA, 12mA, 16mA, 20mA	2.5
LVCMOS18	4mA, 8mA, 12mA, 16mA	1.8
LVCMOS15	4mA, 8mA	1.5
LVCMOS12	2mA, 6mA	1.2
LVCMOS33, Open Drain	4mA, 8mA, 12mA 16mA, 20mA	—
LVCMOS25, Open Drain	4mA, 8mA, 12mA 16mA, 20mA	—
LVCMOS18, Open Drain	4mA, 8mA, 12mA 16mA	—
LVCMOS15, Open Drain	4mA, 8mA	—
LVCMOS12, Open Drain	2mA, 6mA	—
PCI33	N/A	3.3
HSTL18 Class I, II	N/A	1.8
HSTL15 Class I	N/A	1.5
SSTL33 Class I, II	N/A	3.3
SSTL25 Class I, II	N/A	2.5
SSTL18 Class I, II	N/A	1.8
Differential Interfaces		
Differential SSTL33, Class I, II	N/A	3.3
Differential SSTL25, Class I, II	N/A	2.5
Differential SSTL18, Class I, II	N/A	1.8
Differential HSTL18, Class I, II	N/A	1.8
Differential HSTL15, Class I	N/A	1.5
LVDS[1, 2]	N/A	2.5
MLVDS[1]	N/A	2.5
BLVDS[1]	N/A	2.5
LVPECL[1]	N/A	3.3
RSDS[1]	N/A	2.5
LVCMOS33D[1]	4mA, 8mA, 12mA, 16mA, 20mA	3.3

1. Emulated with external resistors.
2. On the left and right edges, LVDS outputs are supported with a dedicated differential output driver on 50% of the I/Os. This solution does not require external resistors at the driver.

Hot Socketing

LatticeXP2 devices have been carefully designed to ensure predictable behavior during power-up and power-down. Power supplies can be sequenced in any order. During power-up and power-down sequences, the I/Os remain in tri-state until the power supply voltage is high enough to ensure reliable operation. In addition, leakage into I/O pins is controlled to within specified limits. This allows for easy integration with the rest of the system. These capabilities make the LatticeXP2 ideal for many multiple power supply and hot-swap applications.

IEEE 1149.1-Compliant Boundary Scan Testability

All LatticeXP2 devices have boundary scan cells that are accessed through an IEEE 1149.1 compliant Test Access Port (TAP). This allows functional testing of the circuit board, on which the device is mounted, through a serial scan path that can access all critical logic nodes. Internal registers are linked internally, allowing test data to be shifted in original backup configuration and try again. This all can be done without power cycling the system. For more information please see TN1220, LatticeXP2 Dual Boot Feature.

For more information on device configuration, please see TN1141, LatticeXP2 sysCONFIG Usage Guide.

Soft Error Detect (SED) Support

LatticeXP2 devices have dedicated logic to perform Cyclic Redundancy Code (CRC) checks. During configuration, the configuration data bitstream can be checked with the CRC logic block. In addition, LatticeXP2 devices can be programmed for checking soft errors in SRAM. SED can be run on a programmed device when the user logic is not active. In the event a soft error occurs, the device can be programmed to either reload from a known good boot image (from internal Flash or external SPI memory) or generate an error signal.

For further information on SED support, please see TN1130, LatticeXP2 Soft Error Detection (SED) Usage Guide.

On-Chip Oscillator

Every LatticeXP2 device has an internal CMOS oscillator that is used to derive a Master Clock (CCLK) for configuration. The oscillator and CCLK run continuously and are available to user logic after configuration is complete. The available CCLK frequencies are listed in Table 2-14. When a different CCLK frequency is selected during the design process, the following sequence takes place:

1. Device powers up with the default CCLK frequency.
2. During configuration, users select a different CCLK frequency.
3. CCLK frequency changes to the selected frequency after clock configuration bits are received.

This internal CMOS oscillator is available to the user by routing it as an input clock to the clock tree. For further information on the use of this oscillator for configuration or user mode, please see TN1141, LatticeXP2 sysCONFIG Usage Guide.

Table 2-14. Selectable CCLKs and Oscillator Frequencies During Configuration and User Mode

CCLK/Oscillator (MHz)
2.5[1]
3.1[2]
4.3
5.4
6.9
8.1
9.2
10
13
15
20
26
32
40
54
80[3]
163[3]

1. Software default oscillator frequency.
2. Software default CCLK frequency.
3. Frequency not valid for CCLK.

Density Shifting

The LatticeXP2 family is designed to ensure that different density devices in the same family and in the same package have the same pinout. Furthermore, the architecture ensures a high success rate when performing design migration from lower density devices to higher density devices. In many cases, it is also possible to shift a lower utilization design targeted for a high-density device to a lower density device. However, the exact details of the final resource utilization will impact the likely success in each case.

Absolute Maximum Ratings[1, 2, 3]

Supply Voltage V_{CC} . . . . -0.5 to 1.32V

Supply Voltage V_{CCAUX} . . . . -0.5 to 3.75V

Supply Voltage V_{CCJ} . . . . -0.5 to 3.75V

Supply Voltage V_{CCPLL}[4] . . . . -0.5 to 3.75V

Output Supply Voltage V_{CCIO} . . . . -0.5 to 3.75V

Input or I/O Tristate Voltage Applied[5] . . . . . . -0.5 to 3.75V

Storage Temperature (Ambient) . . . . -65 to 150°C

Junction Temperature Under Bias (Tj) . . . . +125°C

1. Stress above those listed under the “Absolute Maximum Ratings” may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.
2. Compliance with the Lattice Thermal Management document is required.
3. All voltages referenced to GND.
4. V_{CCPLL} only available on csBGA, PQFP and TQFP packages.
5. Overshoot and undershoot of -2V to (V_{IHMAX} + 2) volts is permitted for a duration of <20 ns.

Recommended Operating Conditions

Symbol	Parameter	Min.	Max.	Units
V_{CC}	Core Supply Voltage	1.14	1.26	V
V_{CCAUX}[4, 5]	Auxiliary Supply Voltage	3.135	3.465	V
V_{CCPLL}[1]	PLL Supply Voltage	3.135	3.465	V
V_{CCIO}[2, 3, 4]	I/O Driver Supply Voltage	1.14	3.465	V
V_{CCJ}[2]	Supply Voltage for IEEE 1149.1 Test Access Port	1.14	3.465	V
t_{JCOM}	Junction Temperature, Commercial Operation	0	85	°C
t_{JIND}	Junction Temperature, Industrial Operation	-40	100	°C

1. V_{CCPLL} only available on csBGA, PQFP and TQFP packages.
2. If V_{CCIO} or V_{CCJ} is set to 1.2 V, they must be connected to the same power supply as V_{CC}. If V_{CCIO} or V_{CCJ} is set to 3.3V, they must be connected to the same power supply as V_{CCAUX}.
3. See recommended voltages by I/O standard in subsequent table.
4. To ensure proper I/O behavior, V_{CCIO} must be turned off at the same time or earlier than V_{CCAUX}.
5. In fpBGA and ftBGA packages, the PLLs are connected to, and powered from, the auxiliary power supply.

On-Chip Flash Memory Specifications

Symbol	Parameter	Max.	Units
$N_{PROGCYC}$	Flash Programming Cycles per $t_{RETENTION}$[1]	10,000	Cycles
	Flash Functional Programming Cycles	100,000	

1. The minimum data retention, $t_{RETENTION}$, is 20 years.

Programming and Erase Flash Supply Current[1, 2, 3, 4, 5]

Over Recommended Operating Conditions

Symbol	Parameter	Device	Typical (25°C, Max. Supply)[6]	Units
I_{CC}	Core Power Supply Current	XP2-5	17	mA
		XP2-8	21	mA
		XP2-17	28	mA
		XP2-30	36	mA
		XP2-40	50	mA
I_{CCAUX}	Auxiliary Power Supply Current[7]	XP2-5	64	mA
		XP2-8	66	mA
		XP2-17	83	mA
		XP2-30	87	mA
		XP2-40	88	mA
I_{CCPLL}	PLL Power Supply Current (per PLL)		0.1	mA
I_{CCIO}	Bank Power Supply Current (per Bank)		5	mA
I_{CCJ}	V_{CCJ} Power Supply Current[8]		14	mA

1. For further information on supply current, please see TN1139, Power Estimation and Management for LatticeXP2 Devices.
2. Assumes all outputs are tristated, all inputs are configured as LVCMOS and held at the V_{CCIO} or GND.
3. Frequency 0 MHz (excludes dynamic power from FPGA operation).
4. A specific configuration pattern is used that scales with the size of the device; consists of 75% PFU utilization, 50% EBR, and 25% I/O configuration.
5. Bypass or decoupling capacitor across the supply.
6. T_J = 25°C, power supplies at nominal voltage.
7. In fpBGA and ftBGA packages the PLLs are connected to and powered from the auxiliary power supply. For these packages, the actual auxiliary supply current is the sum of I_{CCAUX} and I_{CCPLL}. For csBGA, PQFP and TQFP packages the PLLs are powered independent of the auxiliary power supply.
8. When programming via JTAG.

BLVDS

The LatticeXP2 devices support the BLVDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel external resistor across the driver outputs. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3-2 is one possible solution for bi-directional multi-point differential signals.

Figure 3-2. BLVDS Multi-point Output Example

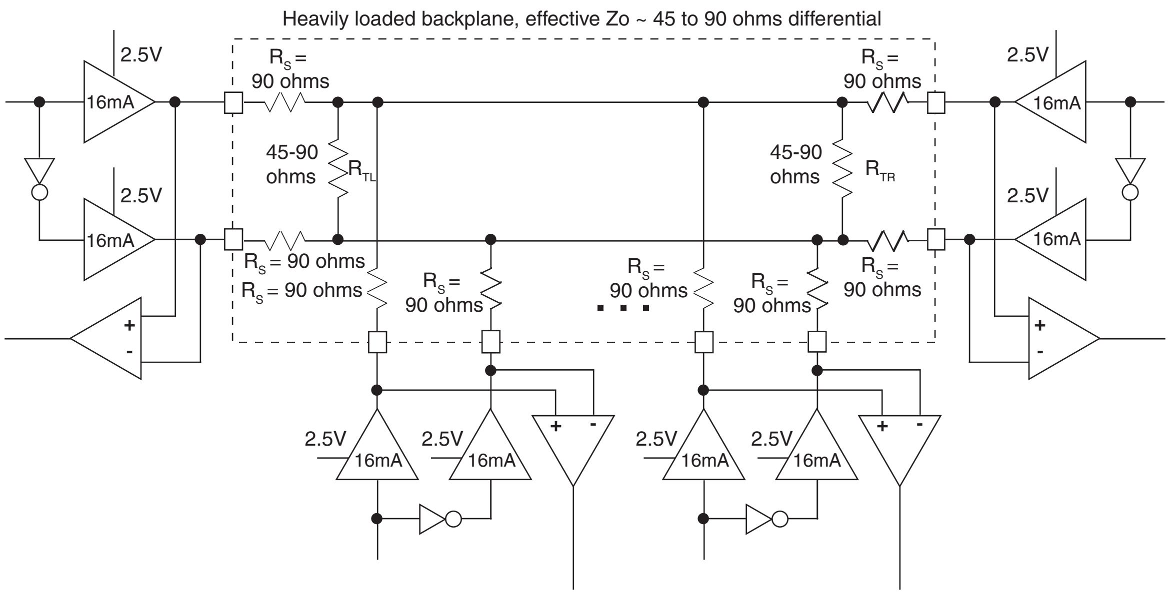


Table 3-2. BLVDS DC Conditions[1]

Over Recommended Operating Conditions

Parameter	Description	Typical		Units
		Zo = 45Ω	Zo = 90Ω	
V_{CCIO}	Output Driver Supply (+/- 5%)	2.50	2.50	V
Z_{OUT}	Driver Impedance	10.00	10.00	Ω
R_S	Driver Series Resistor (+/- 1%)	90.00	90.00	Ω
R_{TL}	Driver Parallel Resistor (+/- 1%)	45.00	90.00	Ω
R_{TR}	Receiver Termination (+/- 1%)	45.00	90.00	Ω
V_{OH}	Output High Voltage (After R_{TL})	1.38	1.48	V
V_{OL}	Output Low Voltage (After R_{TL})	1.12	1.02	V
V_{OD}	Output Differential Voltage (After R_{TL})	0.25	0.46	V
V_{CM}	Output Common Mode Voltage	1.25	1.25	V
I_{DC}	DC Output Current	11.24	10.20	mA

1. For input buffer, see LVDS table.

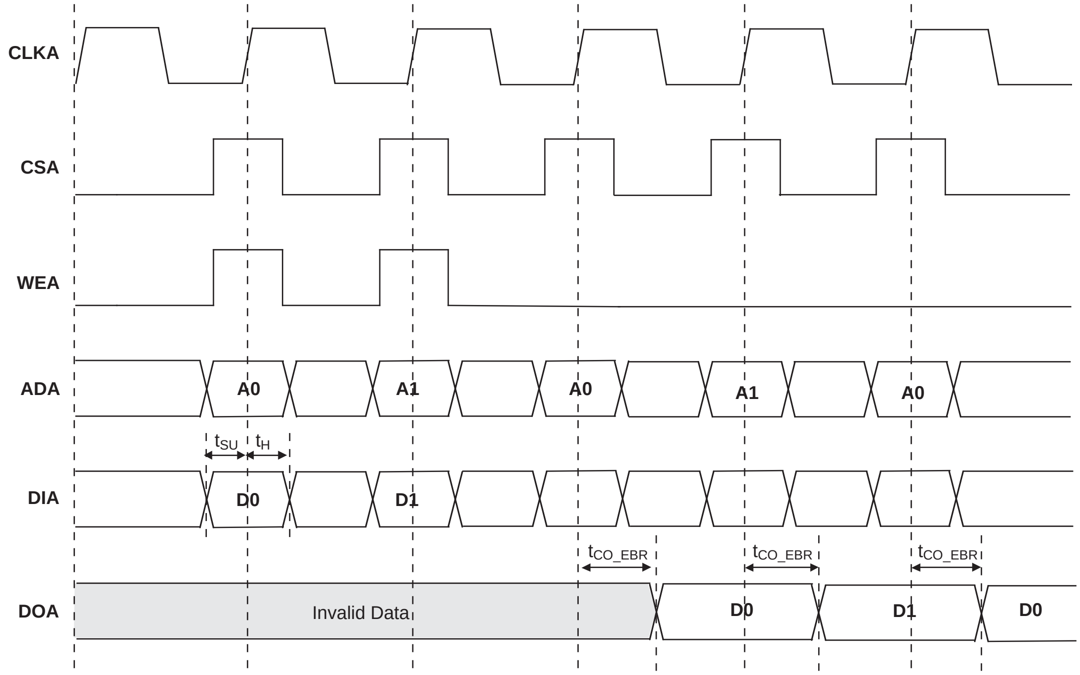
LatticeXP2 Internal Switching Characteristics[1] (Continued)

Over Recommended Operating Conditions

Parameter	Description	-7		-6		-5		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
t_{RST_PIO}	Asynchronous reset time for PFU Logic	—	0.386	—	0.419	—	0.452	ns
t_{DEL}	Dynamic Delay Step Size	0.035	0.035	0.035	0.035	0.035	0.035	ns
EBR Timing								
t_{CO_EBR}	Clock (Read) to Output from Address or Data	—	2.774	—	3.142	—	3.510	ns
t_{COO_EBR}	Clock (Write) to Output from EBR Output Register	—	0.360	—	0.408	—	0.456	ns
t_{SUDATA_EBR}	Setup Data to EBR Memory (Write Clk)	-0.167	—	-0.198	—	-0.229	—	ns
t_{HDATA_EBR}	Hold Data to EBR Memory (Write Clk)	0.194	—	0.231	—	0.267	—	ns
t_{SUADDR_EBR}	Setup Address to EBR Memory (Write Clk)	-0.117	—	-0.137	—	-0.157	—	ns
t_{HADDR_EBR}	Hold Address to EBR Memory (Write Clk)	0.157	—	0.182	—	0.207	—	ns
t_{SUWREN_EBR}	Setup Write/Read Enable to EBR Memory (Write/Read Clk)	-0.135	—	-0.159	—	-0.182	—	ns
t_{HWREN_EBR}	Hold Write/Read Enable to EBR Memory (Write/Read Clk)	0.158	—	0.186	—	0.214	—	ns
t_{SUCE_EBR}	Clock Enable Setup Time to EBR Output Register (Read Clk)	0.144	—	0.160	—	0.176	—	ns
t_{HCE_EBR}	Clock Enable Hold Time to EBR Output Register (Read Clk)	-0.097	—	-0.113	—	-0.129	—	ns
t_{RSTO_EBR}	Reset To Output Delay Time from EBR Output Register (Asynchronous)	—	1.156	—	1.341	—	1.526	ns
t_{SUBE_EBR}	Byte Enable Set-Up Time to EBR Output Register	-0.117	—	-0.137	—	-0.157	—	ns
t_{HBE_EBR}	Byte Enable Hold Time to EBR Output Register Dynamic Delay on Each PIO	0.157	—	0.182	—	0.207	—	ns
t_{RSTREC_EBR}	Asynchronous reset recovery time for EBR	0.233	—	0.291	—	0.347	—	ns
t_{RST_EBR}	Asynchronous reset time for EBR	—	1.156	—	1.341	—	1.526	ns
PLL Parameters								
$t_{RSTKREC\_PLL}$	After RSTK De-assert, Recovery Time Before Next Clock Edge Can Toggle K-divider Counter	1.000	—	1.000	—	1.000	—	ns
t_{RSTREC_PLL}	After RST De-assert, Recovery Time Before Next Clock Edge Can Toggle M-divider Counter (Applies to M-Divider Portion of RST Only[2])	1.000	—	1.000	—	1.000	—	ns
DSP Block Timing								
t_{SUI_DSP}	Input Register Setup Time	0.135	—	0.151	—	0.166	—	ns
t_{HI_DSP}	Input Register Hold Time	0.021	—	-0.006	—	-0.031	—	ns
t_{SUP_DSP}	Pipeline Register Setup Time	2.505	—	2.784	—	3.064	—	ns

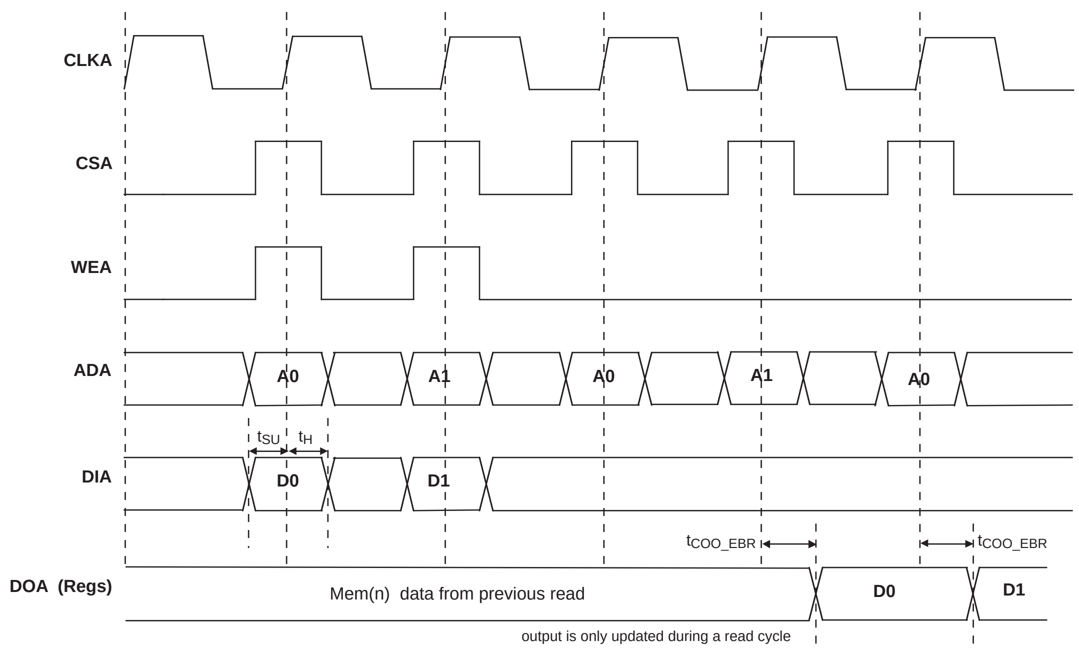
EBR Timing Diagrams

Figure 3-6. Read/Write Mode (Normal)



Note: Input data and address are registered at the positive edge of the clock and output data appears after the positive edge of the clock.

Figure 3-7. Read/Write Mode with Input and Output Registers



sysCLOCK PLL Timing

Over Recommended Operating Conditions

Parameter	Description	Conditions	Min.	Typ.	Max.	Units
f_{IN}	Input Clock Frequency (CLKI, CLKFB)		10	—	435	MHz
f_{OUT}	Output Clock Frequency (CLKOP, CLKOS)		10	—	435	MHz
f_{OUT2}	K-Divider Output Frequency	CLKOK	0.078	—	217.5	MHz
		CLKOK2	3.3	—	145	MHz
f_{VCO}	PLL VCO Frequency		435	—	870	MHz
f_{PFD}	Phase Detector Input Frequency		10	—	435	MHz
AC Characteristics						
t_{DT}	Output Clock Duty Cycle	Default duty cycle selected [3]	45	50	55	%
t_{CPA}	Coarse Phase Adjust		-5	0	5	%
t_{PH} [4]	Output Phase Accuracy		-5	0	5	%
t_{OPJIT} [1]	Output Clock Period Jitter	f_{OUT} > 400 MHz	—	—	±50	ps
		100 MHz < f_{OUT} < 400 MHz	—	—	±125	ps
		f_{OUT} < 100 MHz	—	—	0.025	UIPP
t_{SK}	Input Clock to Output Clock Skew	N/M = integer	—	—	±240	ps
t_{OPW}	Output Clock Pulse Width	At 90% or 10%	1	—	—	ns
t_{LOCK} [2]	PLL Lock-in Time	25 to 435 MHz	—	—	50	µs
		10 to 25 MHz	—	—	100	µs
t_{IPJIT}	Input Clock Period Jitter		—	—	±200	ps
t_{FBKDLY}	External Feedback Delay		—	—	10	ns
t_{HI}	Input Clock High Time	90% to 90%	0.5	—	—	ns
t_{LO}	Input Clock Low Time	10% to 10%	0.5	—	—	ns
t_{RSTKW}	Reset Signal Pulse Width (RSTK)		10	—	—	ns
t_{RSTW}	Reset Signal Pulse Width (RST)		500	—	—	ns

1. Jitter sample is taken over 10,000 samples of the primary PLL output with clean reference clock.
2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.
3. Using LVDS output buffers.
4. Relative to CLKOP.

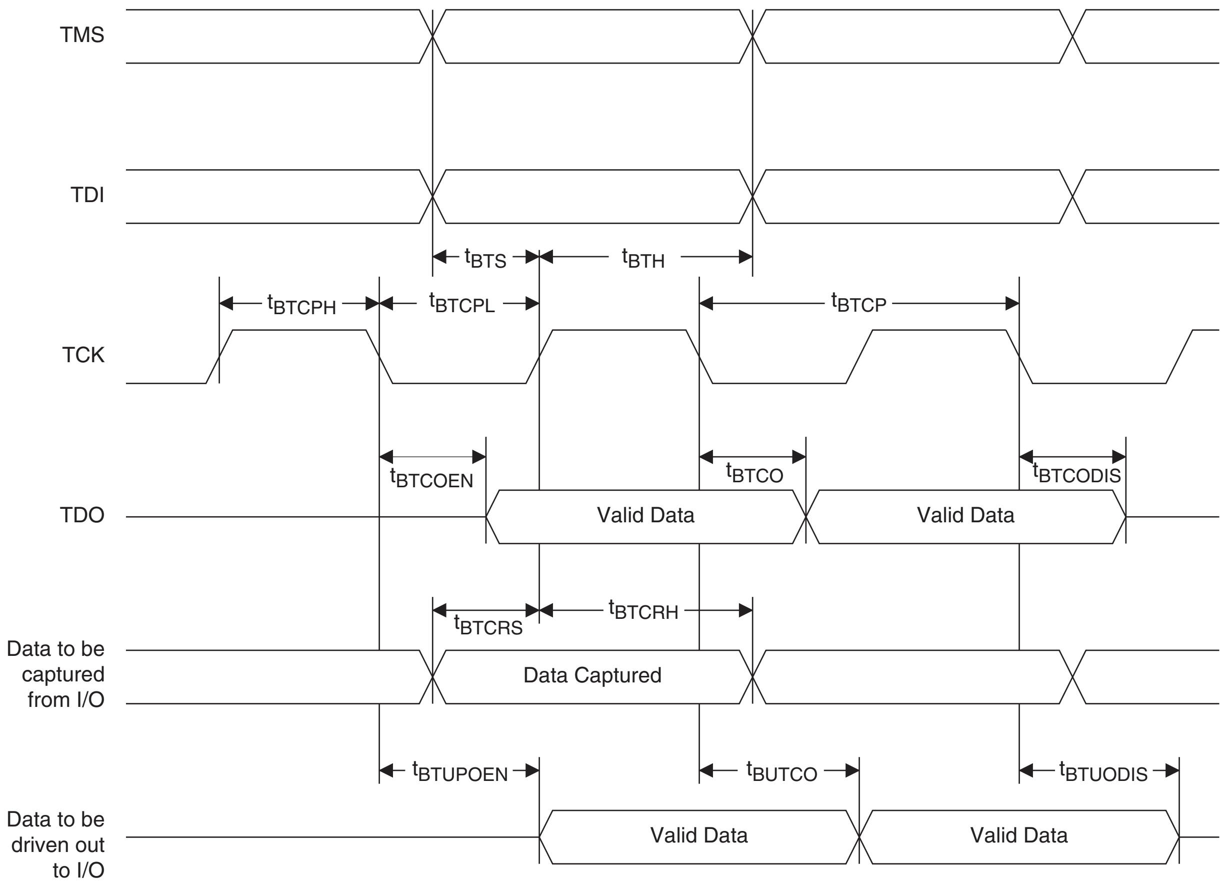
LatticeXP2 sysCONFIG Port Timing Specifications

Over Recommended Operating Conditions

Parameter	Description	Min	Max	Units
sysCONFIG POR, Initialization and Wake Up				
t_{ICFG}	Minimum Vcc to INITN High	—	50	ms
t_{VMC}	Time from t_{ICFG} to valid Master CCLK	—	2	µs
t_{PRGMRJ}	PROGRAMN Pin Pulse Rejection	—	12	ns
t_{PRGM}	PROGRAMN Low Time to Start Configuration	50	—	ns
t_{DINIT}[1]	PROGRAMN High to INITN High Delay	—	1	ms
$t_{DPPINIT}$	Delay Time from PROGRAMN Low to INITN Low	—	50	ns
$t_{DPPDONE}$	Delay Time from PROGRAMN Low to DONE Low	—	50	ns
t_{IODISS}	User I/O Disable from PROGRAMN Low	—	35	ns
t_{IOENSS}	User I/O Enabled Time from CCLK Edge During Wake-up Sequence	—	25	ns
t_{MWC}	Additional Wake Master Clock Signals after DONE Pin High	0	—	Cycles
sysCONFIG SPI Port (Master)				
t_{CFGX}	INITN High to CCLK Low	—	1	µs
t_{CSSPI}	INITN High to CSSPIN Low	—	2	µs
t_{CSCCLK}	CCLK Low before CSSPIN Low	0	—	ns
t_{SOCDO}	CCLK Low to Output Valid	—	15	ns
t_{CSPID}	CSSPIN[0:1] Low to First CCLK Edge Setup Time	2cyc	600+6cyc	ns
f_{MAXSPI}	Max CCLK Frequency	—	20	MHz
t_{SUSPI}	SOSPI Data Setup Time Before CCLK	7	—	ns
t_{HSPI}	SOSPI Data Hold Time After CCLK	10	—	ns
sysCONFIG SPI Port (Slave)				
$f_{MAXSPIS}$	Slave CCLK Frequency	—	25	MHz
t_{RF}	Rise and Fall Time	50	—	mV/ns
t_{STCO}	Falling Edge of CCLK to SOSPI Active	—	20	ns
t_{STOZ}	Falling Edge of CCLK to SOSPI Disable	—	20	ns
t_{STSU}	Data Setup Time (SISPI)	8	—	ns
t_{STH}	Data Hold Time (SISPI)	10	—	ns
t_{STCKH}	CCLK Clock Pulse Width, High	0.02	200	µs
t_{STCKL}	CCLK Clock Pulse Width, Low	0.02	200	µs
t_{STVO}	Falling Edge of CCLK to Valid SOSPI Output	—	20	ns
t_{SCS}	CSSPISN High Time	25	—	ns
t_{SCSS}	CSSPISN Setup Time	25	—	ns
t_{SCSH}	CSSPISN Hold Time	25	—	ns

1. Re-toggling the PROGRAMN pin is not permitted until the INITN pin is high. Avoid consecutive toggling of PROGRAMN.

Figure 3-10. JTAG Port Timing Waveforms



LatticeXP2 Family Data Sheet
Pinout Information

February 2012 **Data Sheet DS1009**

Signal Descriptions

Signal Name	I/O	Description
General Purpose		
P[Edge] [Row/Column Number*]_[A/B]	I/O	[Edge] indicates the edge of the device on which the pad is located. Valid edge designations are L (Left), B (Bottom), R (Right), T (Top). [Row/Column Number] indicates the PFU row or the column of the device on which the PIC exists. When Edge is T (Top) or B (Bottom), only need to specify Row Number. When Edge is L (Left) or R (Right), only need to specify Column Number. [A/B] indicates the PIO within the PIC to which the pad is connected. Some of these user-programmable pins are shared with special function pins. These pins, when not used as special purpose pins, can be programmed as I/Os for user logic. During configuration the user-programmable I/Os are tri-stated with an internal pull-up resistor enabled. If any pin is not used (or not bonded to a package pin), it is also tri-stated with an internal pull-up resistor enabled after configuration.
GSRN	I	Global RESET signal (active low). Any I/O pin can be GSRN.
NC	—	No connect.
GND	—	Ground. Dedicated pins.
V_{CC}	—	Power supply pins for core logic. Dedicated pins.
V_{CCAUX}	—	Auxiliary power supply pin. This dedicated pin powers all the differential and referenced input buffers.
V_{CCPLL}	—	PLL supply pins. csBGA, PQFP and TQFP packages only.
V_{CCIOx}	—	Dedicated power supply pins for I/O bank x.
V_{REF1_x}, V_{REF2_x}	—	Reference supply pins for I/O bank x. Pre-determined pins in each bank are assigned as V_{REF} inputs. When not used, they may be used as I/O pins.
PLL and Clock Functions (Used as user programmable I/O pins when not in use for PLL or clock pins)		
[LOC][num]_V_{CCPLL}	—	Power supply pin for PLL: LLC, LRC, URC, ULC, num = row from center.
[LOC][num]_GPLL[T, C]_IN_A	I	General Purpose PLL (GPLL) input pads: LLC, LRC, URC, ULC, num = row from center, T = true and C = complement, index A,B,C...at each side.
[LOC][num]_GPLL[T, C]_FB_A	I	Optional feedback GPLL input pads: LLC, LRC, URC, ULC, num = row from center, T = true and C = complement, index A,B,C...at each side.
PCLK[T, C]_[n:0]_[3:0]	I	Primary Clock pads, T = true and C = complement, n per side, indexed by bank and 0,1,2,3 within bank.
[LOC]DQS[num]	I	DQS input pads: T (Top), R (Right), B (Bottom), L (Left), DQS, num = ball function number. Any pad can be configured to be output.
Test and Programming (Dedicated Pins)		
TMS	I	Test Mode Select input, used to control the 1149.1 state machine. Pull-up is enabled during configuration.
TCK	I	Test Clock input pin, used to clock the 1149.1 state machine. No pull-up enabled.
TDI	I	Test Data in pin. Used to load data into device using 1149.1 state machine. After power-up, this TAP port can be activated for configuration by sending appropriate command. (Note: once a configuration port is selected it is locked. Another configuration port cannot be selected until the power-up sequence). Pull-up is enabled during configuration.

PICs and DDR Data (DQ) Pins Associated with the DDR Strobe (DQS) Pin

PICs Associated with DQS Strobe	PIO Within PIC	DDR Strobe (DQS) and Data (DQ) Pins
For Left and Right Edges of the Device		
P[Edge] [n-4]	A	DQ
	B	DQ
P[Edge] [n-3]	A	DQ
	B	DQ
P[Edge] [n-2]	A	DQ
	B	DQ
P[Edge] [n-1]	A	DQ
	B	DQ
P[Edge] [n]	A	[Edge]DQSn
	B	DQ
P[Edge] [n+1]	A	DQ
	B	DQ
P[Edge] [n+2]	A	DQ
	B	DQ
P[Edge] [n+3]	A	DQ
	B	DQ
For Top and Bottom Edges of the Device		
P[Edge] [n-4]	A	DQ
	B	DQ
P[Edge] [n-3]	A	DQ
	B	DQ
P[Edge] [n-2]	A	DQ
	B	DQ
P[Edge] [n-1]	A	DQ
	B	DQ
P[Edge] [n]	A	[Edge]DQSn
	B	DQ
P[Edge] [n+1]	A	DQ
	B	DQ
P[Edge] [n+2]	A	DQ
	B	DQ
P[Edge] [n+3]	A	DQ
	B	DQ
P[Edge] [n+4]	A	DQ
	B	DQ

Notes:

1. “n” is a row PIC number.
2. The DDR interface is designed for memories that support one DQS strobe up to 16 bits of data for the left and right edges and up to 18 bits of data for the top and bottom edges. In some packages, all the potential DDR data (DQ) pins may not be available. PIC numbering definitions are provided in the “Signal Names” column of the Signal Descriptions table.

Lead-Free Packaging

Commercial

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-5E-5MN132C	1.2V	-5	Lead-Free csBGA	132	COM	5
LFXP2-5E-6MN132C	1.2V	-6	Lead-Free csBGA	132	COM	5
LFXP2-5E-7MN132C	1.2V	-7	Lead-Free csBGA	132	COM	5
LFXP2-5E-5TN144C	1.2V	-5	Lead-Free TQFP	144	COM	5
LFXP2-5E-6TN144C	1.2V	-6	Lead-Free TQFP	144	COM	5
LFXP2-5E-7TN144C	1.2V	-7	Lead-Free TQFP	144	COM	5
LFXP2-5E-5QN208C	1.2V	-5	Lead-Free PQFP	208	COM	5
LFXP2-5E-6QN208C	1.2V	-6	Lead-Free PQFP	208	COM	5
LFXP2-5E-7QN208C	1.2V	-7	Lead-Free PQFP	208	COM	5
LFXP2-5E-5FTN256C	1.2V	-5	Lead-Free ftBGA	256	COM	5
LFXP2-5E-6FTN256C	1.2V	-6	Lead-Free ftBGA	256	COM	5
LFXP2-5E-7FTN256C	1.2V	-7	Lead-Free ftBGA	256	COM	5

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-8E-5MN132C	1.2V	-5	Lead-Free csBGA	132	COM	8
LFXP2-8E-6MN132C	1.2V	-6	Lead-Free csBGA	132	COM	8
LFXP2-8E-7MN132C	1.2V	-7	Lead-Free csBGA	132	COM	8
LFXP2-8E-5TN144C	1.2V	-5	Lead-Free TQFP	144	COM	8
LFXP2-8E-6TN144C	1.2V	-6	Lead-Free TQFP	144	COM	8
LFXP2-8E-7TN144C	1.2V	-7	Lead-Free TQFP	144	COM	8
LFXP2-8E-5QN208C	1.2V	-5	Lead-Free PQFP	208	COM	8
LFXP2-8E-6QN208C	1.2V	-6	Lead-Free PQFP	208	COM	8
LFXP2-8E-7QN208C	1.2V	-7	Lead-Free PQFP	208	COM	8
LFXP2-8E-5FTN256C	1.2V	-5	Lead-Free ftBGA	256	COM	8
LFXP2-8E-6FTN256C	1.2V	-6	Lead-Free ftBGA	256	COM	8
LFXP2-8E-7FTN256C	1.2V	-7	Lead-Free ftBGA	256	COM	8

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-17E-5QN208C	1.2V	-5	Lead-Free PQFP	208	COM	17
LFXP2-17E-6QN208C	1.2V	-6	Lead-Free PQFP	208	COM	17
LFXP2-17E-7QN208C	1.2V	-7	Lead-Free PQFP	208	COM	17
LFXP2-17E-5FTN256C	1.2V	-5	Lead-Free ftBGA	256	COM	17
LFXP2-17E-6FTN256C	1.2V	-6	Lead-Free ftBGA	256	COM	17
LFXP2-17E-7FTN256C	1.2V	-7	Lead-Free ftBGA	256	COM	17
LFXP2-17E-5FN484C	1.2V	-5	Lead-Free fpBGA	484	COM	17
LFXP2-17E-6FN484C	1.2V	-6	Lead-Free fpBGA	484	COM	17
LFXP2-17E-7FN484C	1.2V	-7	Lead-Free fpBGA	484	COM	17